

**METHOD OF PRODUCING SELF-ALIGNED MASK IN CONJUNCTION
WITH BLOCKING MASK, ARTICLES PRODUCED BY SAME AND
COMPOSITION FOR SAME**

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ABSTRACT OF THE DISCLOSURE

A method of forming a self aligned pattern on an existing pattern on a substrate including applying a coating of a solution containing a masking material in a carrier, the masking material being either photo or thermally
10 sensitive; performing a blanket exposure of the substrate; and allowing at least a portion of the masking material to preferentially develop in a fashion that replicates the existing pattern of the substrate. The existing pattern includes a first set of regions of the substrate having a first reflectivity and a second set of regions of the substrate having a second
15 reflectivity different from the first composition. The first set of regions can include one or more metal elements and the second set of regions can include one or more dielectrics. Structures made in accordance with the method. A low resolution mask is used to block out regions over the substrate. Additionally, the resist can be applied over another masking
20 layer that contains a separate pattern.